

IN THE SPECIFICATION

Please insert the following section after the "FIELD OF INVENTION" section:

--CROSS-REFERENCE TO RELATED APPLICATION

D¹ This application is related to commonly owned copending Provisional Application Serial No. 60/168,155, filed November 29, 1999, and claims the benefit of its earlier filing date under 35 U.S.C. §119(e).--

Please replace the paragraph beginning at line 7 of page 4 with the following rewritten paragraph:

D² --Figure 2 is a diagram illustrating the semiconductor device 200 after a conventional halo implant. Accordingly oftentimes the halo implant 202 ends up providing dopant to all of the source region 204 and drain region 206. Since only the area directly underneath the gate 208 is the area of interest for the implant, there is leakage and other problems associated therewith. Accordingly, the entire active area 212 is open primarily because the thickness of the photoresist mask 213 is such that at a 45° angle, the ultraviolet rays cannot accurately be provided underneath the gate area.--

Please replace the paragraph beginning at line 14 of page 4 with the following rewritten paragraph:

D³ --As is seen, with a photoresist mask 213 thickness of .5 μm , the 45° angle will require that a large portion of the ultraviolet radiation will not reach the area of interest because at that angle, with the thick photoresist, it is not possible. In addition, if a thick photoresist of (0.5 μm or greater) is placed over the trench oxidation 207, due to the soft jelly type nature of the photoresist, oftentimes the photoresist will fall over in the trench oxidation area and cover areas that are to be